



# JCS90N10I

## 主要参数 MAIN CHARACTERISTICS

$I_D$	90A
$V_{DSS}$	100V
$R_{dson-typ}$ (@ $V_{GS}=10V$ )	7.0m $\Omega$
$Q_g-typ$	98nC

### 用途

- 高功率 DC/DC 转换与功率开关
- 直流电机控制
- 汽车应用
- 不间断电源

### 产品特性

- 低栅极电荷
- 低  $R_{dson}$
- 开关速度快
- 产品全部经过雪崩测试
- 高抗  $dv/dt$  能力
- RoHS 产品

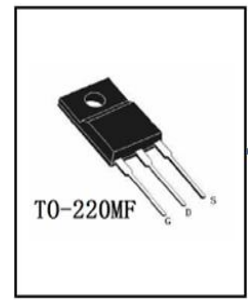
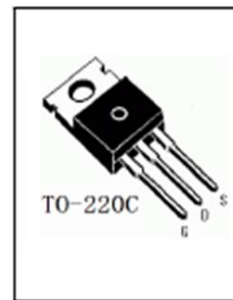
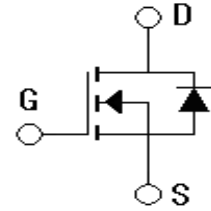
### APPLICATIONS

- High power DC/DC converters and switch mode power supplies
- DC motor control
- Automotive applications
- Uninterruptible power supply

### FEATURES

- Low gate charge
- Low  $R_{dson}$
- Fast switching
- 100% avalanche tested
- Improved  $dv/dt$  capability
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS90N10I-C-B	JCS90N10I-C-BR	N/A	N/A	JCS90N10	TO-220C
JCS90N10I-F-B	JCS90N10I-F-BR	N/A	N/A	JCS90N10	TO-220MF



## 绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		TO-220C	TO-220MF	
最高漏极-源极直流电压 Drain-Source Voltage	V <sub>DSS</sub>	100	100	V
连续漏极电流 Drain Current -continuous	I <sub>D</sub> T=25℃	90*	45*	A
	I <sub>D</sub> T=100℃	72*	36*	A
最大脉冲漏极电流 (注1) Drain Current - pulse (note 1)	I <sub>DM</sub>	360*	180*	A
最高栅源电压 Gate-Source Voltage	V <sub>GSS</sub>	±20		V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	E <sub>AS</sub>	1000		mJ
雪崩电流 (注1) Avalanche Current (note 1)	I <sub>AR</sub>	56		A
重复雪崩能量 (注1) Repetitive Avalanche Current (note 1)	E <sub>AR</sub>	600		mJ
二极管反向恢复最大电压变化 速率 (注3) Peak Diode Recovery dv/dt (note 3)	dv/dt	18		V/ns
耗散功率 Power Dissipation	P <sub>D</sub> T <sub>C</sub> =25℃ -Derate above 25℃	250	37.5	W
		1.67	0.25	W/℃
最高结温及存储温度 Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~+175		℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T <sub>L</sub>	300		℃

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





## 电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
<b>关态特性 Off –Characteristics</b>						
漏—源击穿电压 Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	100	-	-	V
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	1	$\mu A$
		$V_{DS}=100V, V_{GS}=0V,$ $T_C=100^\circ C$	-	-	10	$\mu A$
正向栅极体漏电流 Gate-body leakage current, forward	$I_{GSSF}$	$V_{DS}=0V, V_{GS}=20V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	$I_{GSSR}$	$V_{DS}=0V, V_{GS}=-20V$	-	-	-100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$	-	7.0	9.0	m $\Omega$
正向跨导 Forward Transconductance	$g_{fs}$	$V_{DS} = 40V, I_D=30A$ (note 4)	-	30	-	S
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	$C_{iss}$	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	5600	-	pF
输出电容 Output capacitance	$C_{oss}$		-	750	-	pF
反向传输电容 Reverse transfer capacitance	$C_{rss}$		-	380	-	pF



## 电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=50V, I_D=50A, R_G=25\Omega$ (note 4, 5)	-	53	-	ns
上升时间 Turn-On rise time	$t_r$		-	117	-	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	191	-	ns
下降时间 Turn-Off Fall time	$t_f$		-	110	-	ns
栅极电荷总量 Total Gate Charge	$Q_g$	$V_{DS}=50V,$ $I_D=50A$ $V_{GS}=10V$ (note 4, 5)	-	98	-	nC
栅-源电荷 Gate-Source charge	$Q_{gs}$		-	30	-	nC
栅-漏电荷 Gate-Drain charge	$Q_{gd}$		-	27	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	$I_S$		-	-	90	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$		-	-	360	A
正向压降 Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V,$ $I_S=40A$	-	-	1.2	V
反向恢复时间 Reverse recovery time	$t_{rr}$	$V_{GS}=0V, I_S=50A$ $di_F/dt=100A/\mu s$ (note 4)	-	43	-	ns
反向恢复电荷 Reverse recovery charge	$Q_{rr}$		-	56	-	nC

## 热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max		单 位 Unit
		TO-220C	TO-220MF	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.60	4.0	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	50	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=0.5mH, I_{AS}=45A, V_{DD}=64V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 120A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度  $\leq 300\mu s$ , 占空比  $\leq 2\%$
- 5: 基本与工作温度无关

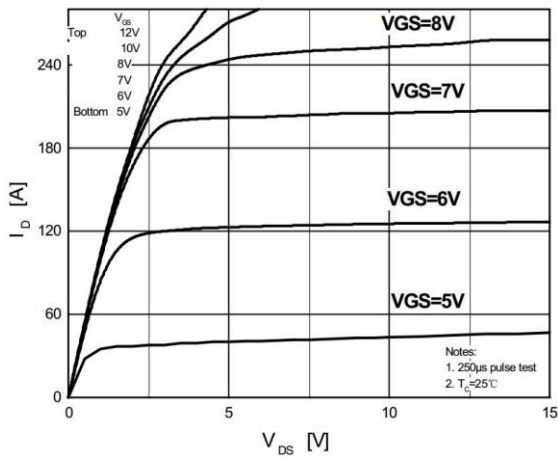
Notes:

- 1: Pulse width limited by maximum junction temperature
- 2:  $L=0.5mH, I_{AS}=45A, V_{DD}=64V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 120A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
- 5: Essentially independent of operating temperature

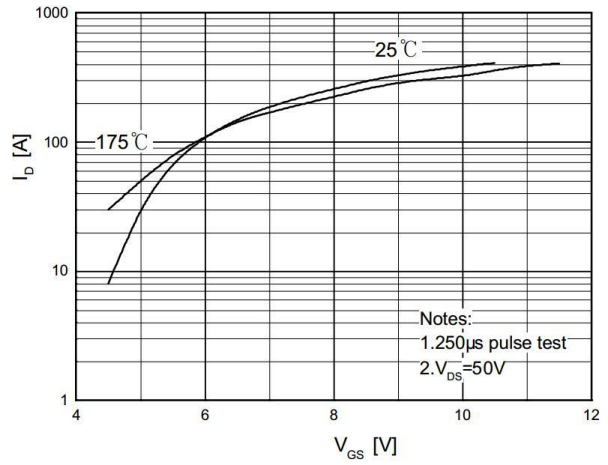


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

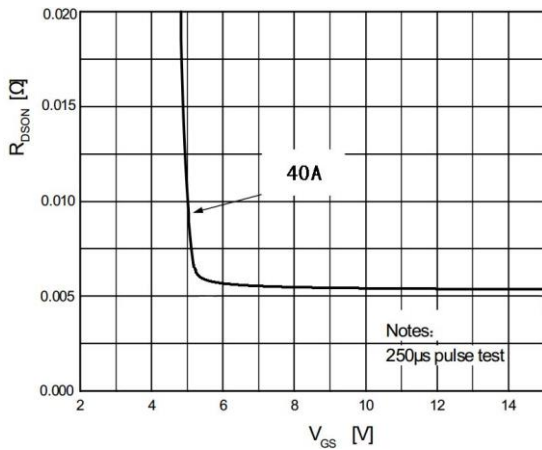
On-Region Characteristics



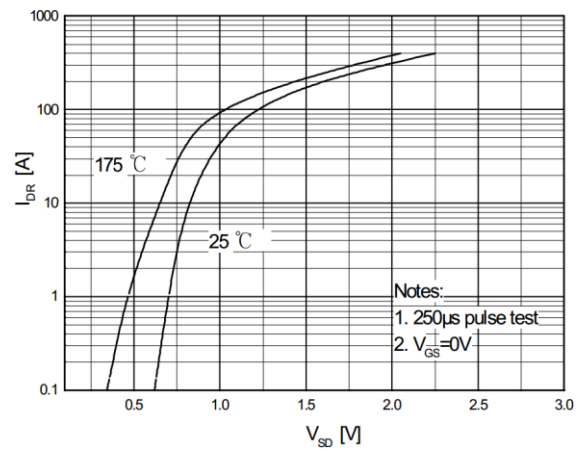
Transfer Characteristics



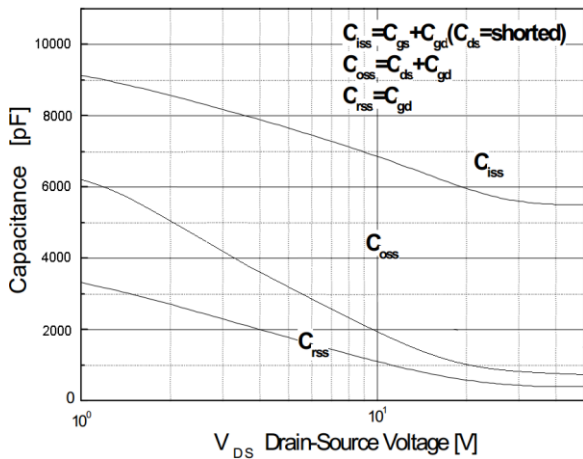
On-Resistance Variation vs. Drain Current and Gate Voltage



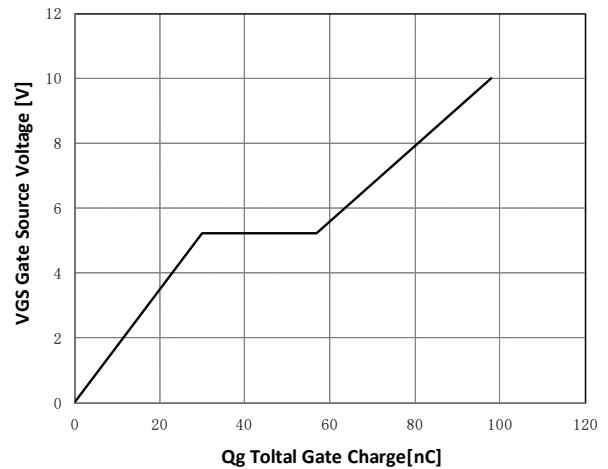
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics



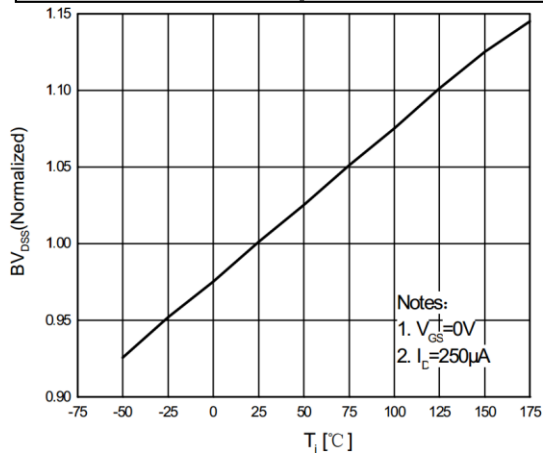
Gate Charge Characteristics



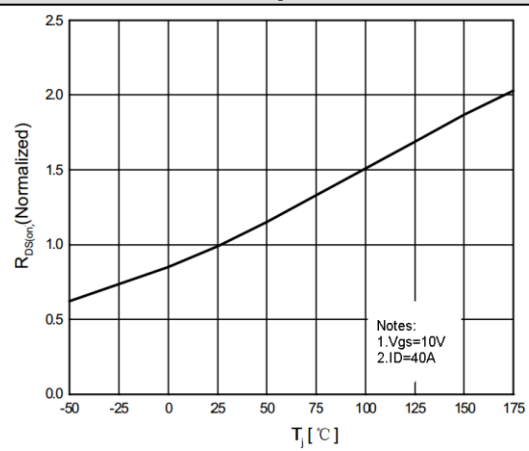


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

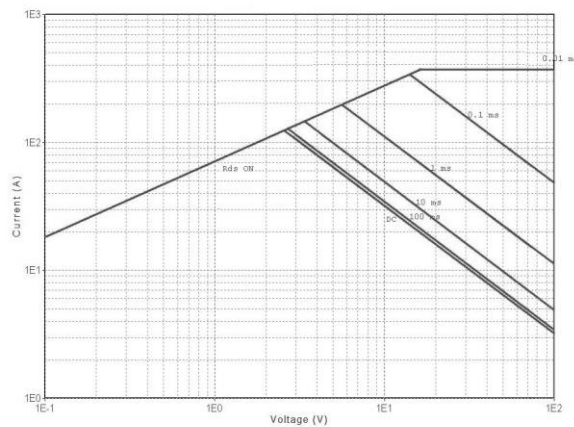
**Breakdown Voltage Variation vs. Temperature**



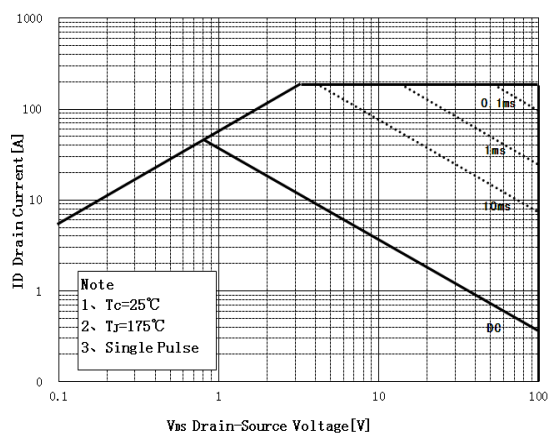
**On-Resistance Variation vs. Temperature**



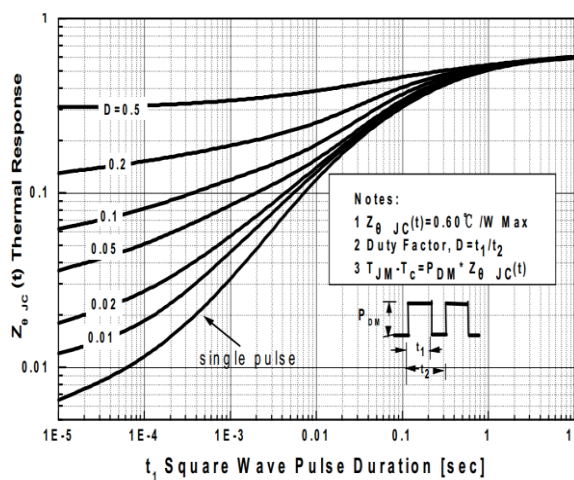
**Maximum Safe Operating Area For JCS90N10I(TO-220C)**



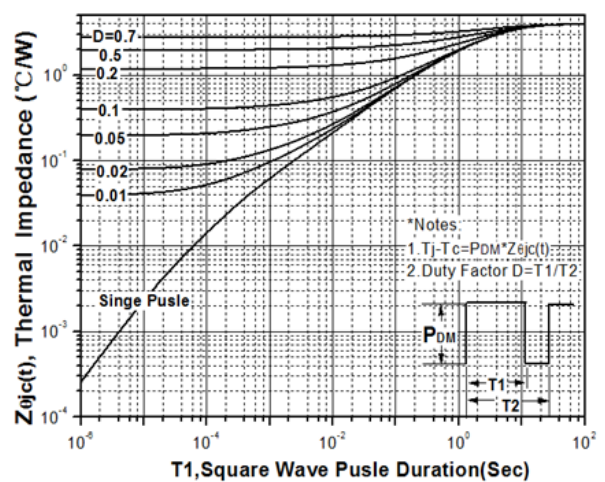
**Maximum Safe Operating Area For JCS90N10I(TO-220MF)**



**Transient Thermal Response Curve For JCS90N10I(TO-220C)**



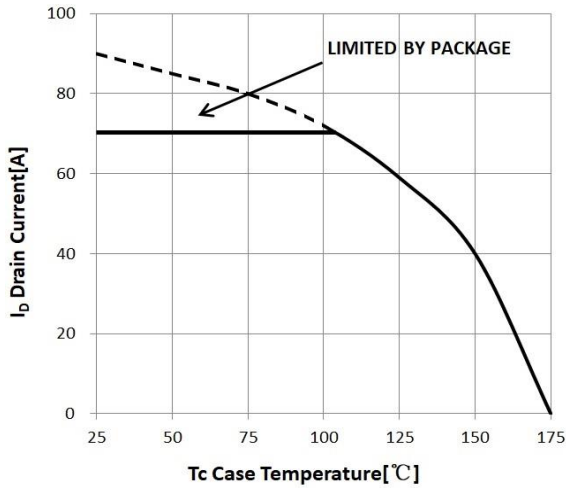
**Transient Thermal Response Curve For JCS90N10I(TO-220MF)**



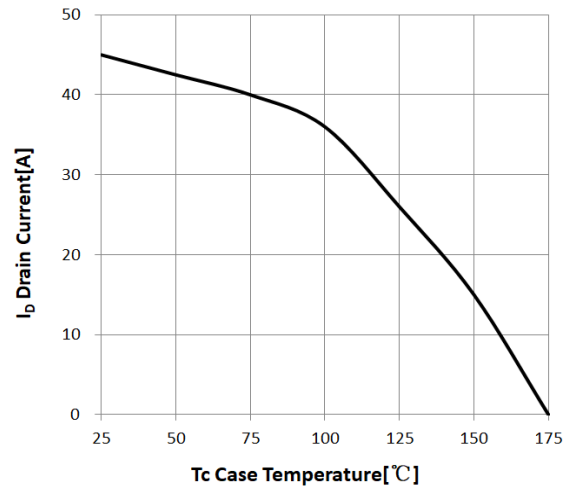


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Maximum Drain Current vs. Case Temperature(TO-220C)



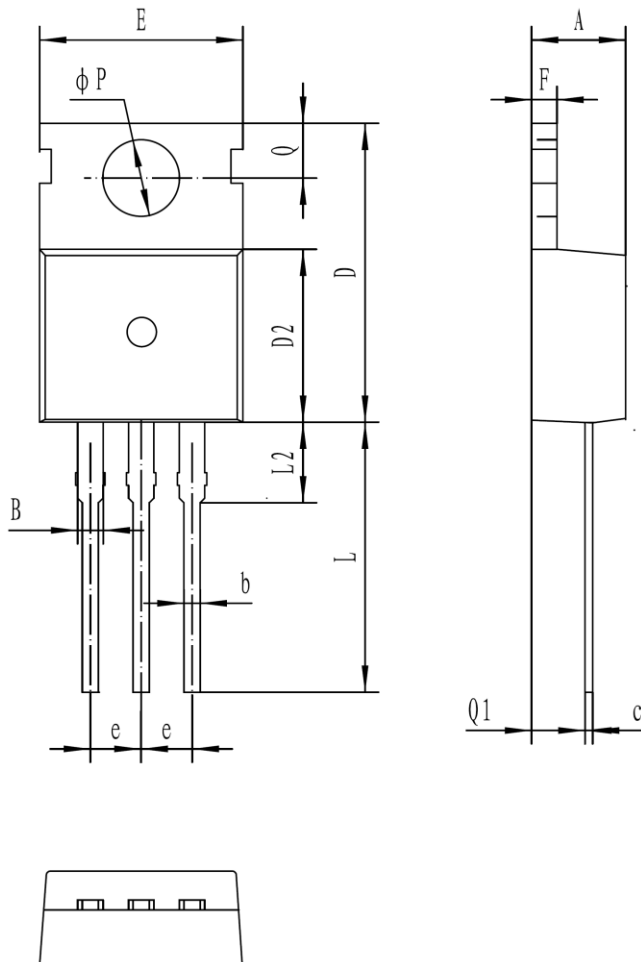
Maximum Drain Current vs. Case Temperature(TO-220C)





TO-220C

单位 Unit: mm



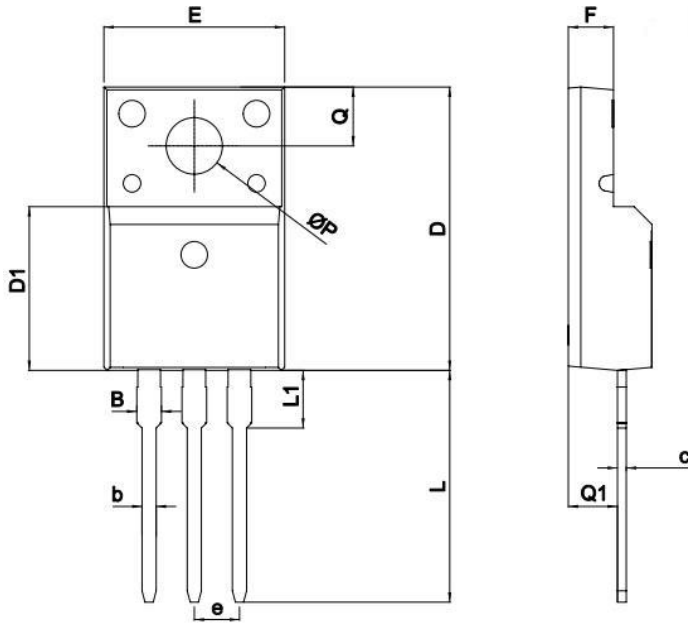
符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80





TO-220MF

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28





### 注意事项

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3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
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